

ABSTRACT

After a rinse process on a wafer W is performed by feeding pure water to the surface of the wafer W at a predetermined flow rate while rotating the wafer W in an approximately horizontal state, a feed amount of the pure water to the wafer W is reduced, and a pure-water feed point is moved outward from the center of the wafer W. In this manner, the wafer W is subjected to a spin dry process while forming a liquid film in a substantially outer region of the pure-water feed point.